## IN THE CLAIMS:

The following is a complete listing of the claims in this application, reflects all changes currently being made to the claims, and replaces all earlier versions and all earlier listings of the claims:

1. (Currently Amended) An image pick-up apparatus comprising a wavelength converter for converting an incident radiation to a light having a wavelength detectable with a photoelectric conversion element on a sensor substrate on which plural photoelectric conversion elements and switching elements are deposited disposed,

wherein a flattening layer having a flat face on which making a contact with the wavelength converter is deposited, is provided between the sensor substrate and wavelength converter.

- 2. (Original) An image pick-up apparatus according to Claim 1, wherein the flattening layer is obtained by flattening a protective layer provided on the sensor substrate.
- 3. (Original) An image pick-up apparatus according to Claim 1, wherein the flattening layer is provided on a protective layer on the sensor substrate.
- 4. (Original) An image pick-up apparatus according to Claim 1, wherein a second flattening layer is provided on the wavelength converter.

5. (Original) An image pick-up apparatus according to Claim 4, wherein the second flattening layer covers the end face of the wavelength converter.

- 6. (Original) An image pick-up apparatus according to Claim 1, wherein the surface of the wavelength converter is flattened.
- 7. (Original) An image pick-up apparatus according to Claim 4, wherein a light reflection film is provided on the second flattening layer.

8. (Original) An image pick-up apparatus according to Claim 6, wherein a light reflection film is provided on the flattened wavelength converter.

- 9. (Original) An image pick-up apparatus according to Claim 1, wherein the wavelength converter comprises a scintillator.
- 10. (Original) An image pick-up apparatus according to Claim 9, wherein the scintillator comprises a columnar crystal.
- 11. (Original) An image pick-up apparatus according to Claim 9, wherein the scintillator comprises a CsI crystal.
- 12. (Original) An image pick-up apparatus according to Claim 7, wherein the light reflection film is made of an aluminum film.

- 13. (Original) An image pick-up apparatus according to Claim 8, wherein the light reflection film is made of an aluminum film.
- 14. (Original) An image pick-up apparatus according to Claim 8, having plural sensor substrates.
- 15. (Currently Amended) An image pick-up apparatus comprising plural sensor substrates on which plural pairs of a photoelectric conversion element and a switching element are <u>deposited</u> <u>disposed</u>,

wherein the plural sensor substrates comprise comprising flattening layers on which a wavelength converter is deposited provided on each flattening layer.

- 16. (Original) An image pick-up apparatus according to Claim 15, wherein a second flattening layer is provided on the wavelength converter.
- 17. (Original) An image pick-up apparatus according to Claim 16, wherein the second flattening layer covers the end face of the wavelength converter.
- 18. (Original) An image pick-up apparatus according to Claim 16, wherein a light reflection film is provided on the second flattening layer.
- 19. (Original) An image pick-up apparatus according to Claim 15, wherein the wavelength converter comprises a scintillator.

- 20. (Original) An image pick-up apparatus according to Claim 19, wherein the scintillator layer comprises a columnar crystal.
- 21. (Original) An image pick-up apparatus according to Claim 20, wherein the scintillator layer comprises a CsI crystal.
- 22. (Original) An image pick-up apparatus according to Claim 18, wherein the light reflection film is made of an aluminum film.

image pick-up apparatus provided with a wavelength converter for converting an incident radiation to a light having a wavelength detectable with a photoelectric conversion element on a sensor substrate on which plural photoelectric conversion elements and switching elements are deposited disposed, wherein a flattening layer having a flat face on which making a contact with the wavelength converter is deposited, is provided between the sensor substrate and wavelength converter, comprising:

a signal processing means for processing the signal from the image pick-up apparatus; and

a display means for displaying the signal from the signal processing means.

24. (Original) An image pick-up system according to Claim 23, further comprising a telecommunication means for transferring the signal from the signal processing means.

25. (Original) An image pick-up apparatus system to Claim 23, further comprising a recording means for recording the signal from the signal processing means.

26. (Original) An image pick-up system according to Claim 23, further comprising a storage means for storing the signal from the signal processing means.

27. (Currently Amended) An image pick-up system comprising:

an image pick-up apparatus comprising plural sensor substrates on
which plural photoelectric conversion elements and switching elements are deposited
disposed, a flattening layer layers being deposited provided on the plural respective sensor
substrates and a wavelength converter being deposited provided on the each flattening
layer, comprising:

a signal processing means for processing the signal from the image pick-up apparatus; and

a display means for displaying the signal from the signal processing means.

- 28. (Original) An image pick-up system according to Claim 27, further comprising a recording means for recording the signal from the signal processing means.
- 29. (Original) An image pick-up system according to Claim 27, further comprising a telecommunication means for transferring the signal from the signal processing means.

30. (Original) An image pick-up system according to Claim 27, further comprising a storage means for storing the signal from the signal processing means.

31. (Currently Amended) A method for manufacturing an image pick-up apparatus comprising the steps of:

forming a protective layer on a sensor substrate on which plural photoelectric conversion elements and switching elements are <u>deposited</u> <del>disposed</del>;

forming a flattening layer having a flat surface on the protective layer; and

depositing forming a wavelength converter on the flattening layer.

32. (Original) A method for manufacturing the image pick-up apparatus according to Claim 31, comprising a step for providing a second flattening layer on the wavelength converter.

- 33. (Original) A method for manufacturing the image pick-up apparatus according to Claim 32, wherein the second flattening layer covers the end face of the wavelength converter.
- 34. (Original) A method for manufacturing the image pick-up apparatus according to Claim 31, comprising a step of flattening the wavelength converter.

35. (Original) A method for manufacturing the image pick-up apparatus according to Claim 32, comprising a step for providing a light reflection film on the second flattening layer.

36. (Original) A method for manufacturing the image pick-up apparatus according to Claim 34, comprising a step of providing a light reflection film on the flattened wavelength converter.

37. (Original) A method for manufacturing the image pick-up apparatus according to Claim 31, wherein the step for forming the wavelength converter comprises a vacuum deposition step.

38. (Currently Amended) A method for manufacturing the image pick-up apparatus comprising the steps of:

forming a protective layer on a sensor substrate on which plural photoelectric conversion elements and switching elements are <u>deposited</u> <del>disposed</del>;

layer.

flattening the surface of the protective layer; and

depositing forming a scintillator layer on the flattened protective

39. (Original) A method for manufacturing the image pick-up apparatus according to Claim 38, comprising the steps of forming a second flattening layer on the wavelength converter.

40. (Original) A method for manufacturing the image pick-up apparatus according to Claim 39, wherein the second flattening layer covers the end face of the wavelength converter.

- 41. (Original) A method for manufacturing the image pick-up apparatus according to Claim 38, comprising the step of flattening the wavelength converter.
- 42. (Original) A method for manufacturing the image pick-up apparatus according to Claim 39, comprising the step of forming a reflection film on the second flattening layer.

43. (Original) A method for manufacturing the image pick-up apparatus according to Claim 41, comprising the step of forming a light reflection film on the flattened wavelength converter.

- 44. (Original) A method for manufacturing the image pick-up apparatus according to Claim 38, wherein the step for forming the wavelength converter comprises a vapor deposition step.
- 45. (Currently Amended) A method for manufacturing an image pick-up apparatus comprising the steps of:

providing disposing plural sensor substrates on which plural pairs of a photoelectric conversion element and a switching element are deposited disposed, a flattening layer being formed on the respective plural sensor substrates; and

depositing providing a wavelength converter on the flattened layer.

- 46. (Original) A method for manufacturing an image pick-up apparatus according to Claim 45, comprising the step of forming a second flattening layer on the wavelength converter.
- 47. (Original) A method for manufacturing an image pick-up apparatus according to Claim 46, wherein the second flattening layer is provided so as to cover the end face of the scintillator layer.

48. (Original) A method for manufacturing an image pick-up apparatus according to Claim 46, comprising a step of providing a light reflection layer on the second flattening layer.

- 49. (Original) A method for manufacturing an image pick-up apparatus according to Claim 45, wherein the step for providing the wavelength converter comprises a vacuum deposition step.
- 50. (Original) A method for manufacturing an image pick-up apparatus according to Claim 45, wherein the wavelength converter comprises a scintillator made of a columnar crystal.
- 51. (Original) A method for manufacturing an image pick-up apparatus according to Claim 45, wherein the wavelength converter comprises a CsI crystal.

52. (New) An image pick-up apparatus comprising a wavelength converter for converting an incident radiation to a light having a wavelength detectable with a photoelectric conversion element on a sensor substrate on which plural photoelectric conversion elements and switching elements are deposited,

wherein a flattening layer having a flat face on which the wavelength converter is deposited, is provided between the sensor substrate and wavelength converter, and

wherein the photoelectric conversion elements comprise non-single crystalline semiconductor material.

53. (New) The image pick-up apparatus according to Claim 52, wherein the photoelectric conversion elements comprise an amorphous silicon film.